SiA477EDJT

Vishay Siliconix

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P-Channel 12 V (D-S) MOSFET

Thin PowerPAK[®] SC-70-6L Single D 0.6 mm 4 2.05 mm Top View Bottom View



Marking code: B7

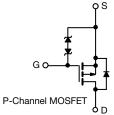
PRODUCT SUMMARY									
V _{DS} (V)	-12								
$R_{DS(on)}$ max. (Ω) at V_{GS} = -4,5 V	0.0130								
$R_{DS(on)}$ max. (Ω) at V_{GS} = -3.7 V	0.0145								
$R_{DS(on)}$ max. (Ω) at V_{GS} = -2.5 V	0.0190								
$R_{DS(on)}$ max. (Ω) at V_{GS} = -1.8 V	0.0320								
Q _g typ. (nC)	33								
I _D (A)	-12								
Configuration	Single								

FEATURES

- TrenchFET[®] Gen III p-channel power MOSFET
- Thermally enhanced PowerPAK® SC-70 package - Small footprint area - Low on-resistance
- 100 % R_q tested
- R_{DS(on)} rating at V_{GS} = -1.8 V
- Built in ESD protection with Zener diode
- Typical ESD performance: 3500 V
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Smart phones, tablet PCs, mobile computing
 - Battery switch
 - Charger switch
 - Load switch



ORDERING INFORMATION

Package	Thin PowerPAK SC-70-6L						
Lead (Pb)-free and halogen-free	SiA477EDJT-T1-GE3						

ABSOLUTE MAXIMUM RATINGS	(T _A = 25 °C, unless	otherwise note	d)	
PARAMETER		SYMBOL LIMIT		UNIT
Drain-source voltage		V _{DS}	-12	V
Gate-source voltage		V _{GS}	± 8	v
	T _C = 25 °C		-12 ^a	
Continuous dusin surrent (T. 150 °C)	T _C = 70 °C		-12 ^a	
Continuous drain current (T _J = 150 °C)	T _A = 25 °C	I _D	-12 ^{a, b, c}	
	T _A = 70 °C		-11 ^{b, c}	A
Pulsed drain current (t = 100 µs)		I _{DM}	-50	
	T _C = 25 °C		-12 ^a	
Continuous source-drain diode current	T _A = 25 °C	I _S	-2.9 ^{b, c}	
	T _C = 25 °C		19	
Movinum nouser dissinction	T _C = 70 °C		12	w
Maximum power dissipation	T _A = 25 °C	P _D	3.5 ^{b, c}	vv
	T _A = 70 °C	1	2.2 ^{b, c}	
Operating junction and storage temperature rar	nge	T _J , T _{stg}	-55 to +150	
Soldering recommendations (peak temperature) d, e		260	

THERMAL RESISTANCE RATINGS								
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT			
Maximum junction-to-ambient b, f	t ≤ 5 s	R _{thJA}	28	36	°C 4M			
Maximum junction-to-case (drain)	Steady state	R _{thJC}	5.3	6.5	°C/W			

Notes Package limited

a. b. Surface mounted on 1" x 1" FR4 board

t = 5 s

See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection d.

Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

e. f. Maximum under steady state conditions is 80 °C/W

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Document Number: 77703



RoHS

COMPLIANT HALOGEN

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SiA477EDJT

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT			
Static	0111202				117 0 11				
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = -250 μA	-12	-	-	V			
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$		-	-3.9	_	mV/°C			
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = -250 μA	_	2.5	_				
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-0.4	-	-1	V			
	GO(III)	$V_{DS} = 0 V, V_{GS} = \pm 8 V$	-	-	± 12	-			
Gate-source leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 4.5 V$	-	-	± 1				
		$V_{DS} = -12 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	-1	μA			
Zero gate voltage drain current	I _{DSS}	$V_{DS} = -12 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$	-	-	-10				
On-state drain current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, \text{ V}_{GS} = -4.5 \text{ V}$	-20	-	-	А			
	2(0.1)	$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -5 \text{ A}$	-	0.0110	0.0130				
	-	$V_{GS} = -3.7 \text{ V}, I_D = -5 \text{ A}$	-	0.0114	0.0145				
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = -2.5 \text{ V}, \text{ I}_{D} = -3 \text{ A}$	-	0.0145	0.0190	Ω			
		V _{GS} = -1.8 V, I _D = -1 A	-	0.0228	0.0320	-			
Forward transconductance a	9 _{fs}	$V_{DS} = -6 V, I_D = -5 A$	-	30	-	S			
Dynamic ^b	010				J	1			
Input capacitance	C _{iss}		-	3050	-				
Output capacitance	C _{oss}	V _{DS} = -6 V, V _{GS} = 0 V, f = 1 MHz	-	725	-	pF			
Reverse transfer capacitance	C _{rss}		-	740	-				
· · · ·		$V_{DS} = -6 V$, $V_{GS} = -10 V$, $I_{D} = -10 A$	-	55	83	nC			
Total gate charge	Qg		-	33	50				
Gate-source charge	Q _{qs}	$V_{DS} = -6 \text{ V}, \text{ V}_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -10 \text{ A}$	-	4.3	-				
Gate-drain charge	Q _{gd}		-	8.9	-				
Gate resistance	Rg	f = 1 MHz	1.2	6	12	Ω			
Turn-on delay time	t _{d(on)}		-	25	50				
Rise time	tr	$V_{DD} = -6 V, R_I = 1 \Omega$	-	25	50				
Turn-off delay time	t _{d(off)}	$I_D \cong -10 \text{ A}, \text{ V}_{\text{GEN}} = -4.5 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$	-	70	140				
Fall time	t _f		-	50	100				
Turn-on delay time	t _{d(on)}		-	10	20	ns			
Rise time	t _r	$V_{DD} = -10 \text{ V}, \text{ R}_{1} = 1 \Omega$	-	20	40	1			
Turn-off delay time	t _{d(off)}	$I_D \cong -10 \text{ A}, V_{GEN} = -8 \text{ V}, R_g = 1 \Omega$	-	90	180				
Fall time	t _f		-	46	90	1			
Drain-Source Body Diode Characterist	ics		•		•	1			
Continuous source-drain diode current	Is	T _C = 25 °C	-	-	-12				
Pulse diode forward current	I _{SM}		-	-	-50	A			
Body diode voltage	V _{SD}	I _S = -10 A, V _{GS} = 0 V	-	-0.8	-1.2	V			
Body diode reverse recovery time	t _{rr}		-	60	120	ns			
Body diode reverse recovery charge	Q _{rr}	I _F = -10 A, di/dt = 100 A/μs,	-	39	80	nC			
Reverse recovery fall time	ta			22	-	1			
Reverse recovery rise time	t _b		-	38	-	ns			

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

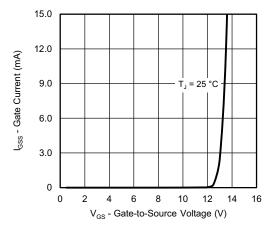
b. Guaranteed by design, not subject to production testing

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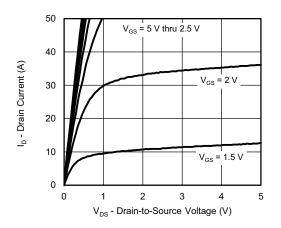
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



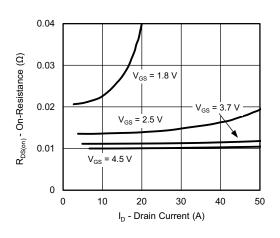
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



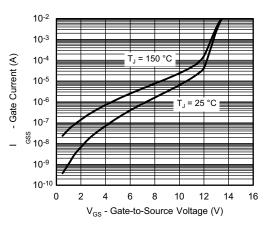
Gate Current vs. Gate-Source Voltage



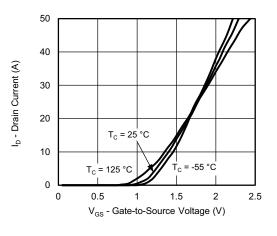
Output Characteristics



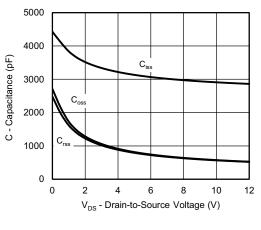
On-Resistance vs. Drain Current



Gate Current vs. Gate-Source Voltage



Transfer Characteristics



Capacitance

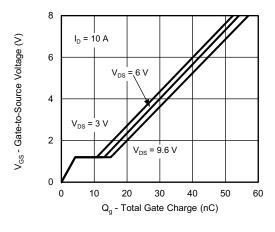
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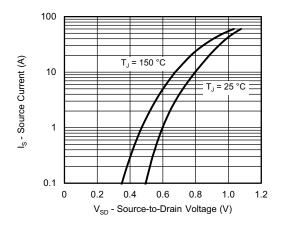
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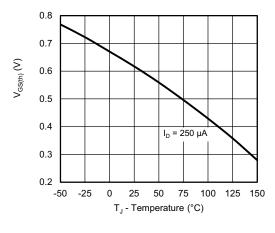
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



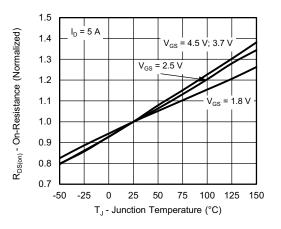
Gate Charge



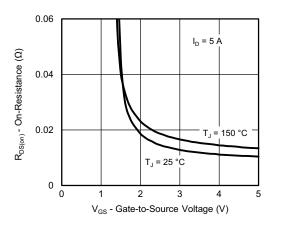
Source-Drain Diode Forward Voltage



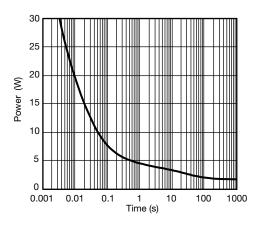
Threshold Voltage



On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient

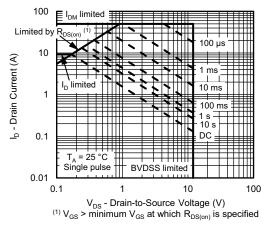
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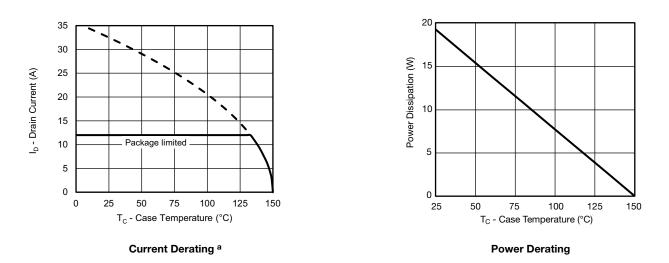
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Safe Operating Area, Junction-to-Ambient

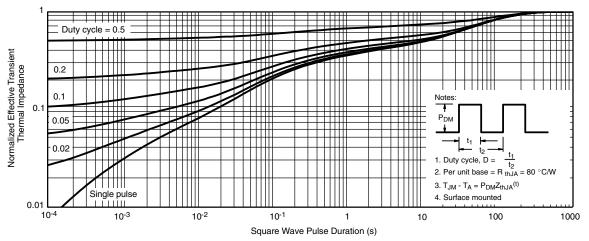


Note

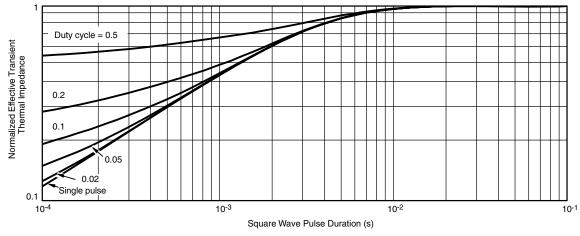
a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

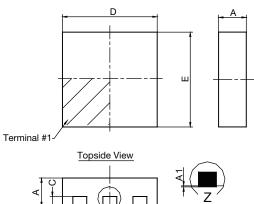


Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?77703.

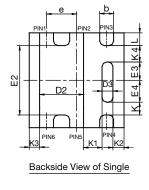


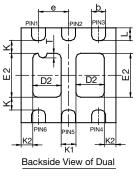
Case Outline for PowerPAK® SC70T



Side View







	SINGLE PAD						DUAL PAD						
DIM.	MILLIMETERS			INCHES			MILLIMETERS			INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	0.525	0.60	0.65	0.0206	0.024	0.026	0.525	0.60	0.65	0.0206	0.024	0.026	
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
D2	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028	
D3	0.135	0.235	0.335	0.005	0.009	0.013							
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
E2	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041	
E3	0.345	0.395	0.445	0.014	0.016	0.018							
E4	0.425	0.475	0.525	0.017	0.019	0.021							
е		0.65 BSC			0.026 BSC		0.65 BSC			0.026 BSC			
К		0.275 TYP.			0.011 TYP.		0.275 TYP.			0.011 TYP.			
K1		0.400 TYP.			0.016 TYP.		0.320 TYP.			0.013 TYP.			
K2		0.240 TYP.			0.009 TYP.			0.252 TYP.			0.010 TYP.		
K3		0.225 TYP.		0.009 TYP.									
K4		0.355 TYP.		0.014 TYP.									
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015	
Т							0.05	0.10	0.15	0.002	0.004	0.006	
ECN: C1 DWG: 59		v. B, 05-Ma	ar-12										

Notes

1. All dimensions are in millimeter. Millimeters will govern.

2. Package outline exculsive of mold flash and metal burr.

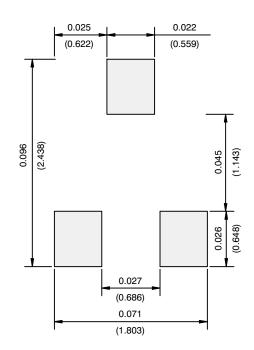
3. Package outline inclusive of plating



Application Note 826

Vishay Siliconix

RECOMMENDED MINIMUM PADS FOR SC-70: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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Application Note 826

Vishay Siliconix



RECOMMENDED MINIMUM PADS FOR SC-70: 6-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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